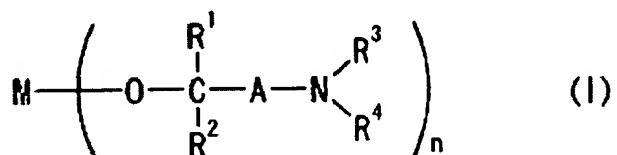


## ABSTRACT OF THE DISCLOSURE

An alkoxide compound of formula (I) suitable as a material for thin film formation used in thin film formation involving vaporization of a material such as CVD, a material for thin film formation including the alkoxide compound, and a process for thin film formation using the material. The process includes vaporizing the material for thin film formation, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.



wherein one of R<sup>1</sup> and R<sup>2</sup> represents an alkyl group having 1-4 carbon atoms, the other representing a hydrogen atom or an alkyl group having 1-4 carbon atoms; R<sup>3</sup> and R<sup>4</sup> each represent an alkyl group having 1-4 carbon atoms; A represents an alkanediyl group having 1-8 carbon atoms; M represents a silicon atom or a hafnium atom; and n represents 4.